



# SPP3407B

## P-Channel Enhancement Mode MOSFET

### DESCRIPTION

The SPP3407B is the P-Channel logic enhancement mode power field effect transistors are produced using high cell density , DMOS trench technology.

This high density process is especially tailored to minimize on-state resistance.

These devices are particularly suited for low voltage application such as cellular phone and notebook computer power management and other battery powered circuits, and low in-line power loss are needed in a very small outline surface mount package.

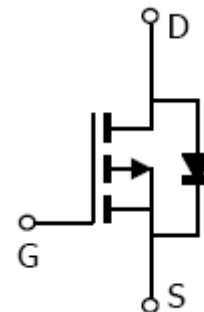
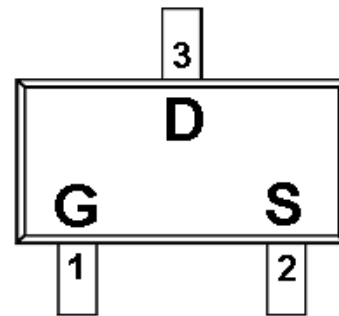
### FEATURES

- ◆  $-30\text{V}/-4.0\text{A}, R_{\text{DS(ON)}}=70\text{m}\Omega @ V_{\text{GS}}=-10\text{V}$
- ◆  $-30\text{V}/-3.2\text{A}, R_{\text{DS(ON)}}=95\text{m}\Omega @ V_{\text{GS}}=-4.5\text{V}$
- ◆ Super high density cell design for extremely low  $R_{\text{DS(ON)}}$
- ◆ Exceptional on-resistance and maximum DC current capability
- ◆ SOT-23-3L package design

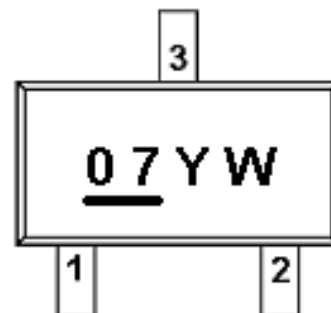
### APPLICATIONS

- Power Management in Note book
- Portable Equipment
- Battery Powered System
- DC/DC Converter
- Load Switch
- DSC
- LCD Display inverter

### PIN CONFIGURATION(SOT-23-3L)



### PART MARKING



Y : Year Code  
W : Week Code



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### PIN DESCRIPTION

Pin	Symbol	Description
1	G	Gate
2	S	Source
3	D	Drain

### ORDERING INFORMATION

Part Number	Package	Part Marking
SPP3407BS23RGB	SOT-23-3L	<u>07</u>

※ Week Code : A ~ Z( 1 ~ 26 ) ; a ~ z( 27 ~ 52 )

※ SPP3407BS23RGB : Tape Reel ; Pb – Free; Halogen – Free

### ABSOLUTE MAXIMUM RATINGS

(TA=25°C Unless otherwise noted)

Parameter	Symbol	Typical	Unit	
Drain-Source Voltage	V <sub>DSS</sub>	-30	V	
Gate –Source Voltage	V <sub>GSS</sub>	±20	V	
Continuous Drain Current(T <sub>J</sub> =150°C)	I <sub>D</sub>	TA=25°C	-3.6	A
		TA=70°C	-3.0	
Pulsed Drain Current	I <sub>DM</sub>	-15	A	
Continuous Source Current(Diode Conduction)	I <sub>S</sub>	-1.0	A	
Power Dissipation	P <sub>D</sub>	TA=25°C	1.25	W
		TA=70°C	0.8	
Operating Junction Temperature	T <sub>J</sub>	150	°C	
Storage Temperature Range	T <sub>STG</sub>	-55/150	°C	
Thermal Resistance-Junction to Ambient	R <sub>θJA</sub>	120	°C/W	



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### ELECTRICAL CHARACTERISTICS

(TA=25°C Unless otherwise noted)

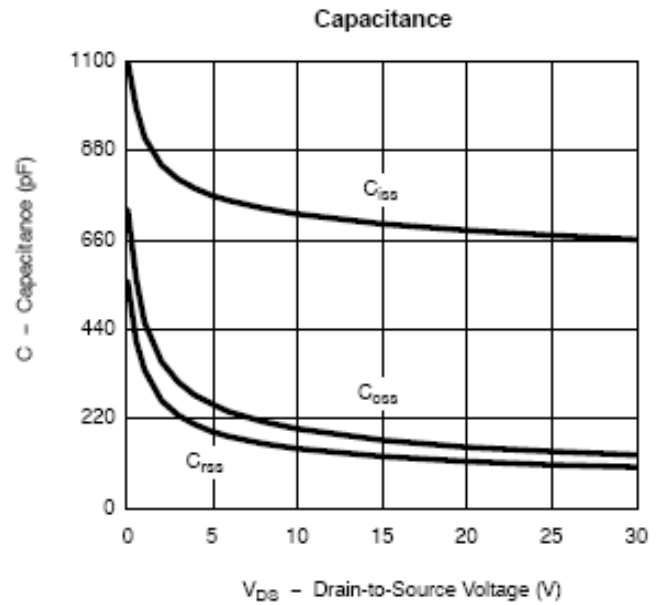
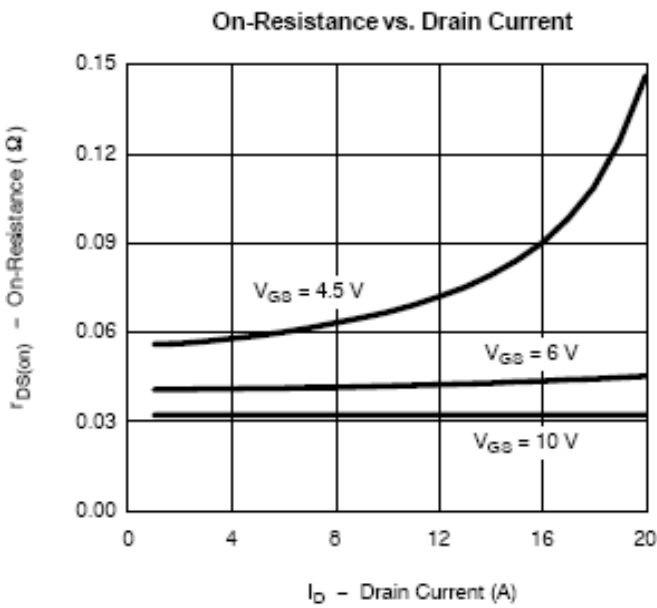
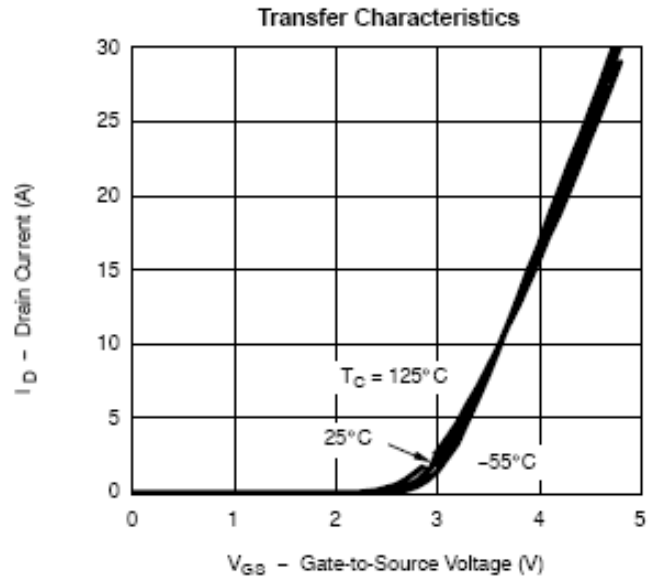
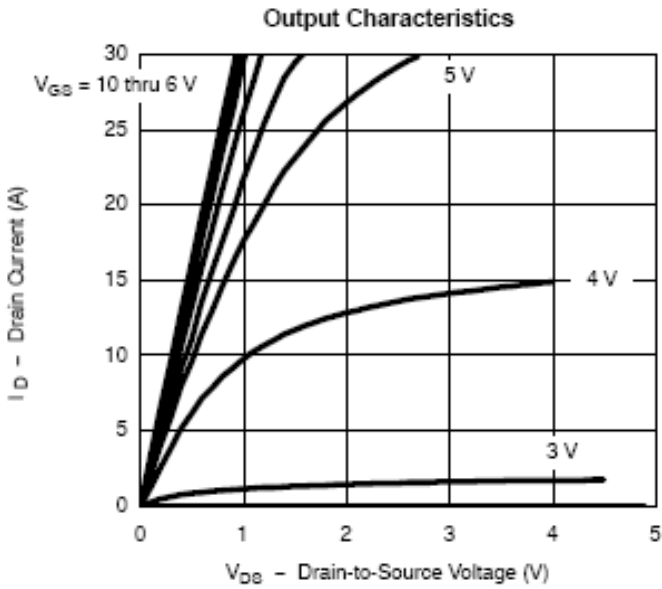
Parameter	Symbol	Conditions	Min.	Typ	Max.	Unit
<b>Static</b>						
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	$V_{GS}=0V, I_D=-250\mu A$	-30			V
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}, I_D=-250\mu A$	-0.8		-2.5	
Gate Leakage Current	$I_{GSS}$	$V_{DS}=0V, V_{GS}=\pm 20V$			$\pm 100$	nA
Zero Gate Voltage Drain Current	$I_{DSS}$	$V_{DS}=-24V, V_{GS}=0V$			-1	uA
		$V_{DS}=-24V, V_{GS}=0V$ $T_J=55^\circ C$			-10	
On-State Drain Current	$I_{D(on)}$	$V_{DS} \leq -5V, V_{GS}=-10V$	-10			A
Drain-Source On-Resistance	$R_{DS(on)}$	$V_{GS}=-10V, I_D=-4.0A$		0.062	0.070	$\Omega$
		$V_{GS}=-4.5V, I_D=-3.2A$		0.085	0.095	
Forward Transconductance	$g_{fs}$	$V_{DS}=-5.0V, I_D=-4.0A$		10		S
Diode Forward Voltage	$V_{SD}$	$I_S=-1.0A, V_{GS}=0V$		-0.8	-1.2	V
<b>Dynamic</b>						
Total Gate Charge	$Q_g$	$V_{DS}=-15V, V_{GS}=-10V$ $I_D=-3.5A$		10	18	nC
Gate-Source Charge	$Q_{gs}$			1.6		
Gate-Drain Charge	$Q_{gd}$			3.0		
Input Capacitance	$C_{iss}$	$V_{DS}=-15V, V_{GS}=0V$ $f=1MHz$		450		pF
Output Capacitance	$C_{oss}$			95		
Reverse Transfer Capacitance	$C_{rss}$			55		
Turn-On Time	$t_{d(on)}$	$V_{DD}=-15V, R_L=15\Omega$ $I_D=-1.0A, V_{GEN}=-10V$ $R_G=6\Omega$		8	18	nS
	$t_r$			8	18	
Turn-Off Time	$t_{d(off)}$			25	50	
	$t_f$			25	35	



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### TYPICAL CHARACTERISTICS

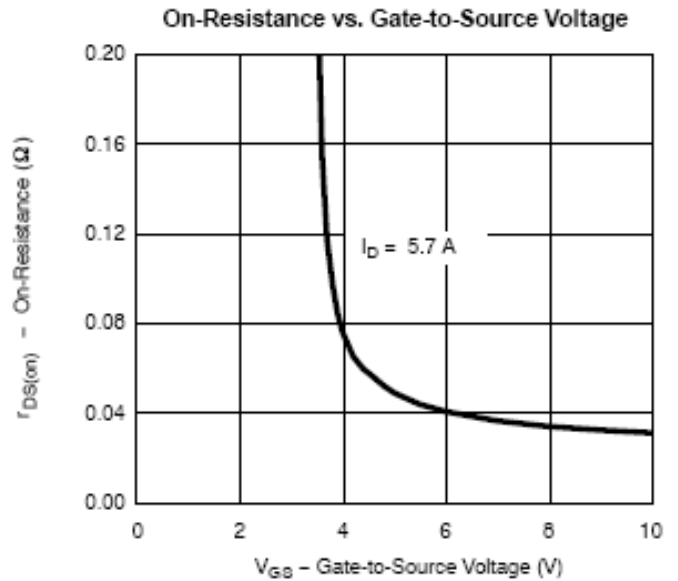
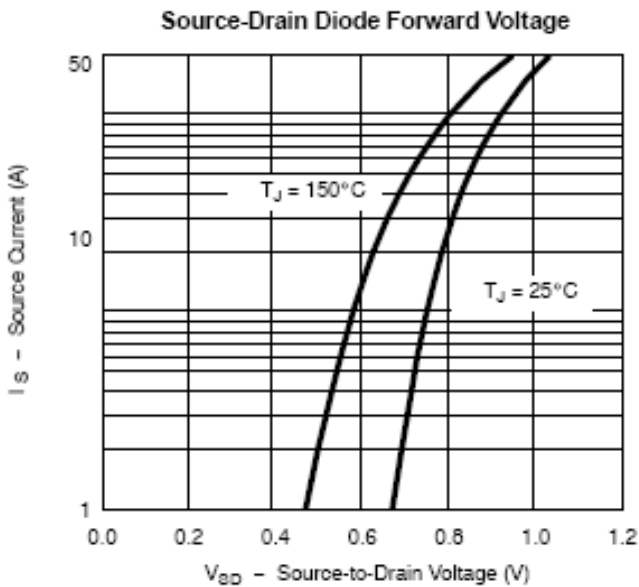
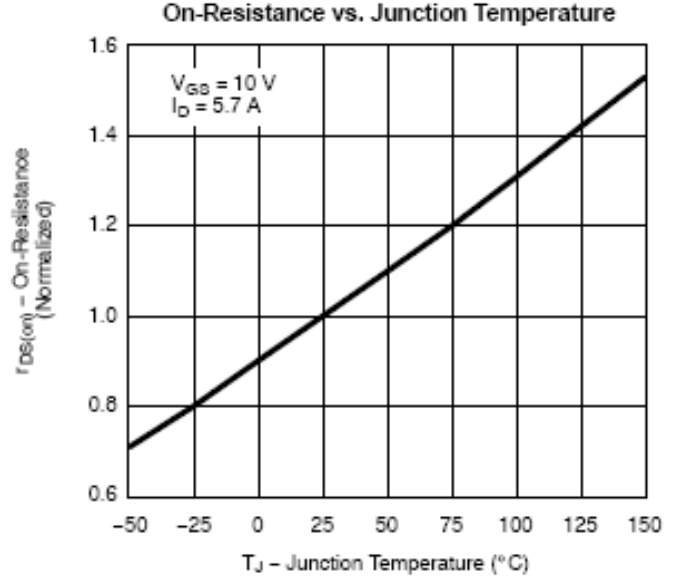
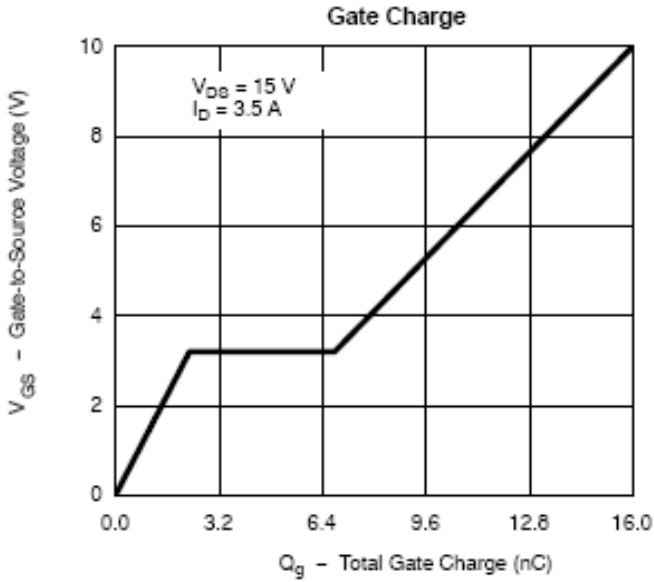




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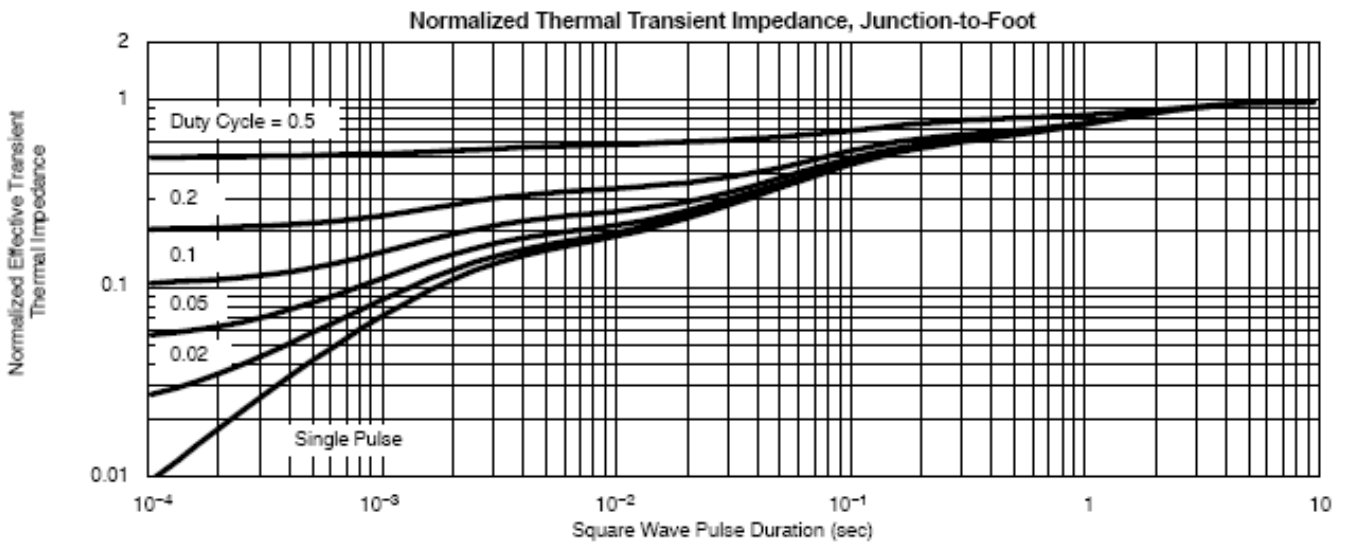
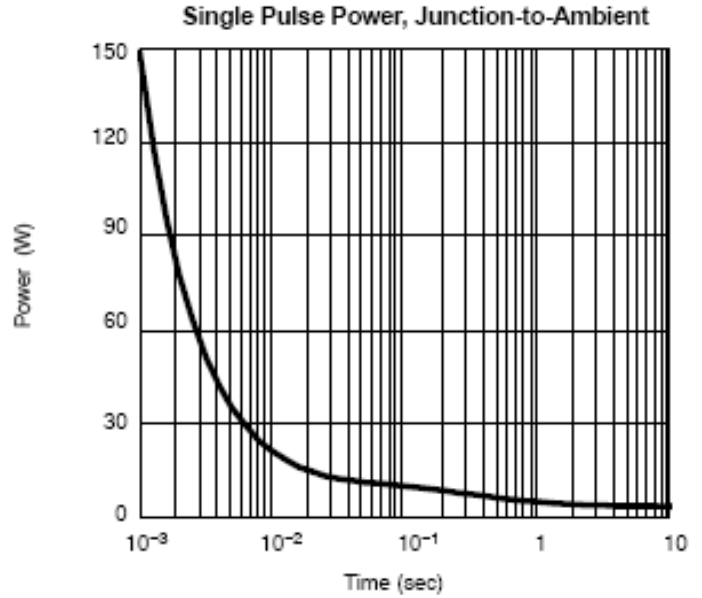
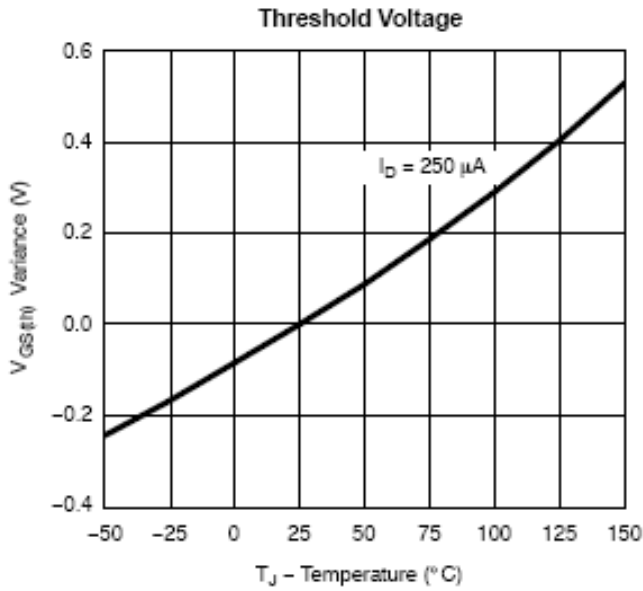




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### TYPICAL CHARACTERISTICS





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